



## N-Channel NexFET™ Power MOSFETs

 Check for Samples: **CSD16403Q5A**

### FEATURES

- Ultra Low  $Q_g$  and  $Q_{gd}$
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5mm x 6mm Plastic Package

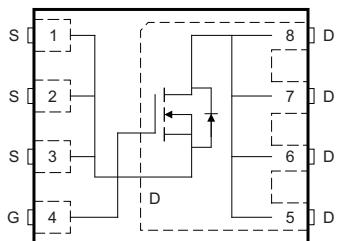
### APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control FET Applications

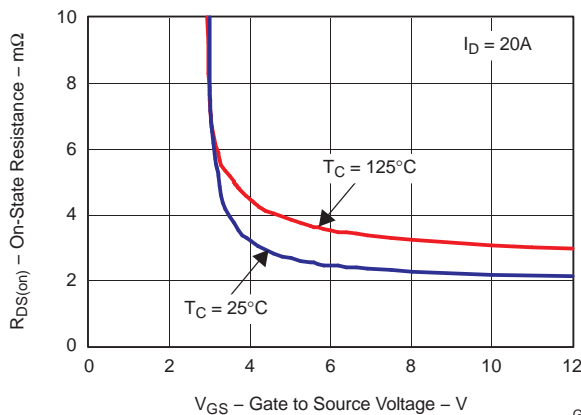
### DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.

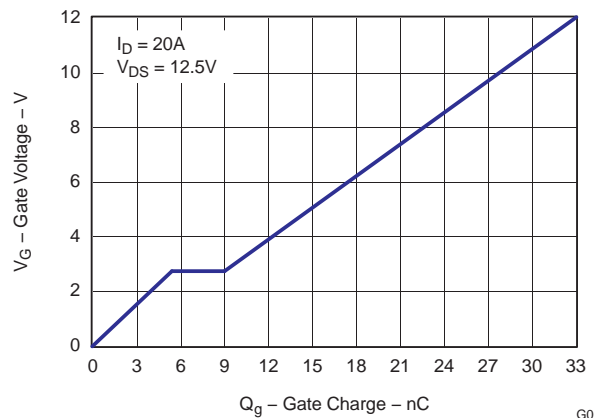
Top View



P0093-01

 **$R_{DS(ON)}$  vs  $V_{GS}$** 


G006

**Gate Charge**


G003

### PRODUCT SUMMARY

$V_{DS}$	Drain to Source Voltage	25	V
$Q_g$	Gate Charge Total (4.5V)	13.3	nC
$Q_{gd}$	Gate Charge Gate to Drain	3.5	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 4.5V$	2.9 mΩ
		$V_{GS} = 10V$	2.2 mΩ
$V_{GS(th)}$	Threshold Voltage	1.6	V

### ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16403Q5A	SON 5X6 Plastic Package	13-inch reel	2500	Tape and Reel

### ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ unless otherwise stated		VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	25	V
$V_{GS}$	Gate to Source Voltage	+16 / -12	V
$I_D$	Continuous Drain Current, $T_C = 25^\circ\text{C}$	100	A
	Continuous Drain Current <sup>(1)</sup>	28	A
$I_{DM}$	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ <sup>(2)</sup>	184	A
$P_D$	Power Dissipation <sup>(1)</sup>	3.1	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$E_{AS}$	Avalanche Energy, single pulse $I_D = 67A, L = 0.1\text{mH}, R_G = 25\Omega$	224	mJ

 (1)  $R_{\theta JA} = 41^\circ\text{C/W}$  on 1in<sup>2</sup> Cu FR4 PCB.

 (2) Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ 


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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>Static Characteristics</b>						
$V_{DSS}$	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
$I_{DSS}$	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$			1	$\mu A$
$I_{GSS}$	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +16/-12V$			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.6	1.9	V
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 20A$		2.9	3.7	m $\Omega$
		$V_{GS} = 10V, I_D = 20A$		2.2	2.8	m $\Omega$
$g_{fs}$	Transconductance	$V_{DS} = 15V, I_D = 20A$		91		S
<b>Dynamic Characteristics</b>						
$C_{ISS}$	Input Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V, f = 1MHz$		2040	2660	pF
$C_{OSS}$	Output Capacitance			1600	2080	pF
$C_{RSS}$	Reverse Transfer Capacitance			115	160	pF
$R_g$	Series Gate Resistance			1.2	2.4	$\Omega$
$Q_g$	Gate Charge Total (4.5V)	$V_{DS} = 12.5V, I_D = 20A$		13.3	18	nC
$Q_{gd}$	Gate Charge Gate to Drain			3.5		nC
$Q_{gs}$	Gate Charge Gate to Source			5.5		nC
$Q_{g(th)}$	Gate Charge at $V_{th}$			3.1		nC
$Q_{OSS}$	Output Charge	$V_{DS} = 13.5V, V_{GS} = 0V$		33		nC
$t_{d(on)}$	Turn On Delay Time	$V_{DS} = 12.5V, V_{GS} = 4.5V, I_D = 20A, R_G = 2\Omega$		11.8		ns
$t_r$	Rise Time			18.3		ns
$t_{d(off)}$	Turn Off Delay Time			15.2		ns
$t_f$	Fall Time			9.2		ns
<b>Diode Characteristics</b>						
$V_{SD}$	Diode Forward Voltage	$I_S = 20A, V_{GS} = 0V$		0.8	1.0	V
$Q_{rr}$	Reverse Recovery Charge	$V_{DD} = 13.5V, I_F = 20A, di/dt = 300A/\mu s$		47		nC
$t_{rr}$	Reverse Recovery Time	$V_{DD} = 13.5V, I_F = 20A, di/dt = 300A/\mu s$		35		ns

## THERMAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			1.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>(1) (2)</sup>			51	$^\circ\text{C/W}$

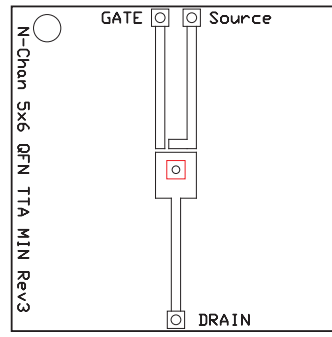
(1)  $R_{\theta JC}$  is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in 0.060 inch thick FR4 board.  $R_{\theta JC}$  is specified by design while  $R_{\theta JA}$  is determined by the user's board design.

(2) Device mounted on FR4 Material with 1 inch<sup>2</sup> of 2 oz. Cu.



M0137-01

Max  $R_{\theta JA} = 51^{\circ}\text{C/W}$   
when mounted on 1  
 $\text{inch}^2$  of 2 oz. Cu.

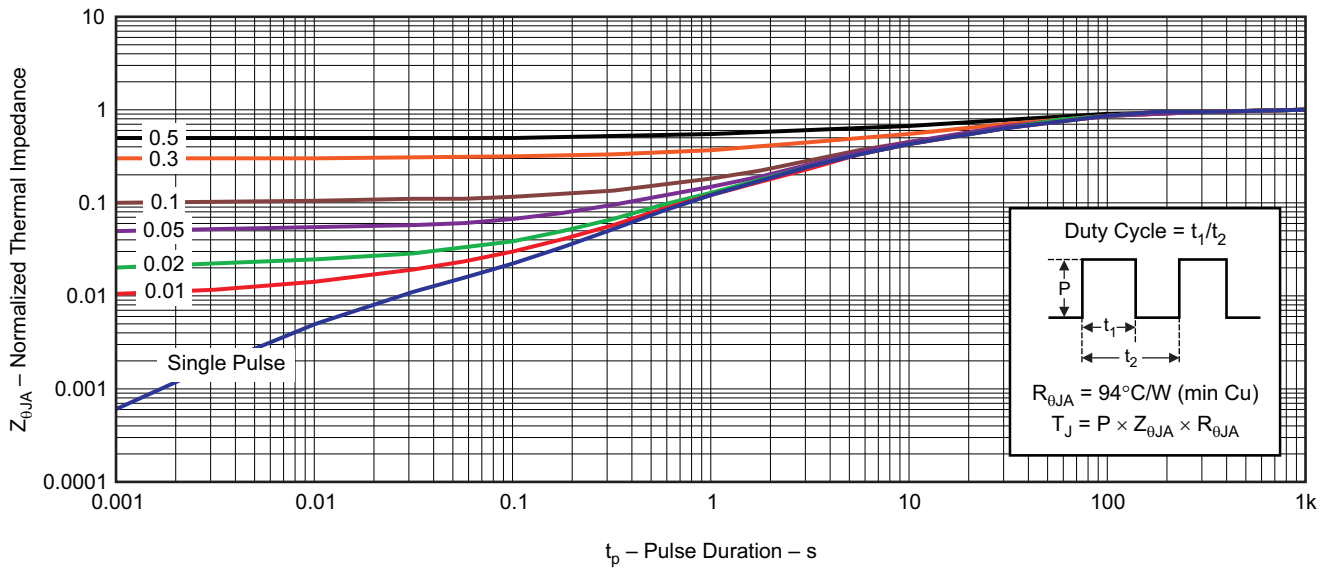


M0137-02

Max  $R_{\theta JA} = 118^{\circ}\text{C/W}$   
when mounted on  
minimum pad area of 2  
oz. Cu.

### TYPICAL MOSFET CHARACTERISTICS

( $T_A = 25^{\circ}\text{C}$  unless otherwise stated)

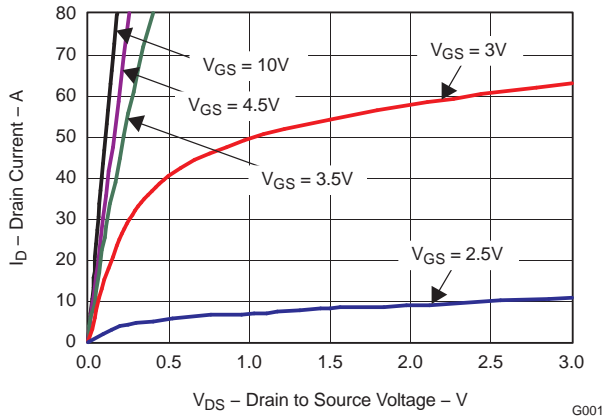


G012

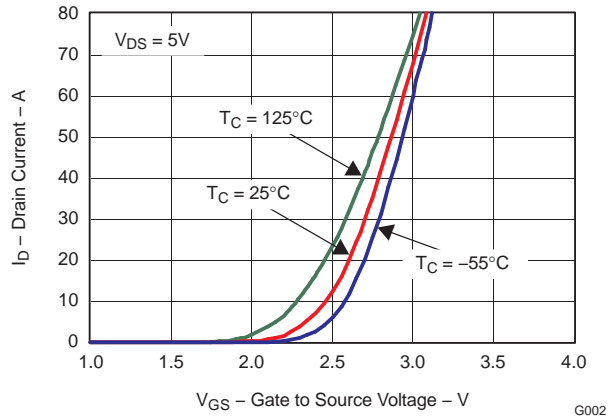
Figure 1. Transient Thermal Impedance

**TYPICAL MOSFET CHARACTERISTICS (continued)**

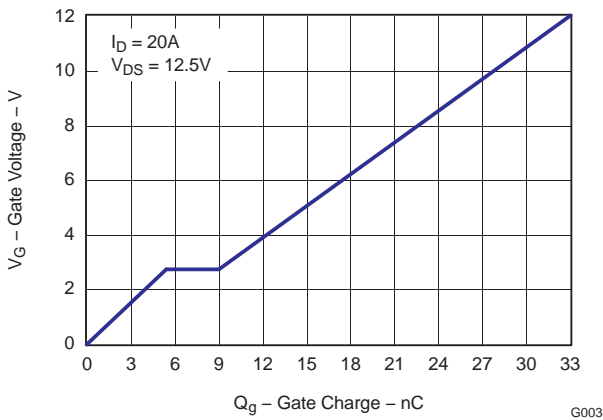
( $T_A = 25^\circ\text{C}$  unless otherwise stated)



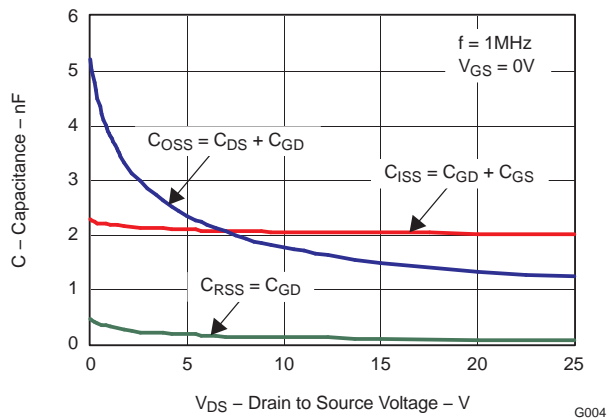
**Figure 2. Saturation Characteristics**



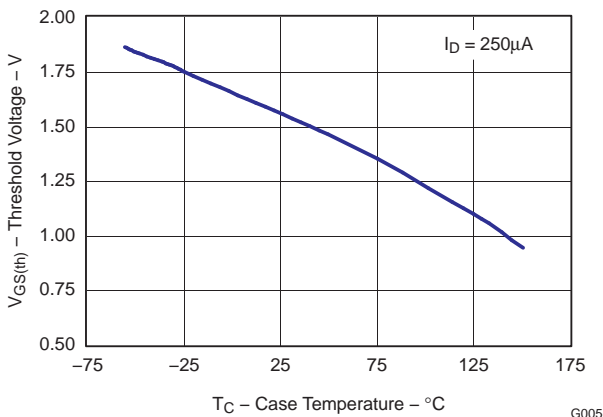
**Figure 3. Transfer Characteristics**



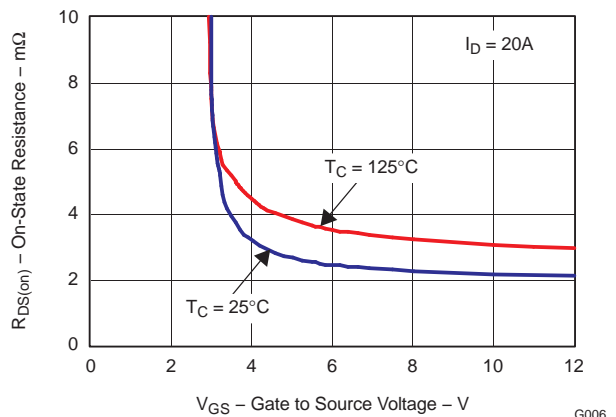
**Figure 4. Gate Charge**



**Figure 5. Capacitance**



**Figure 6. Threshold Voltage vs Temperature**



**Figure 7. On Resistance vs Gate Voltage**

TYPICAL MOSFET CHARACTERISTICS (continued)

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

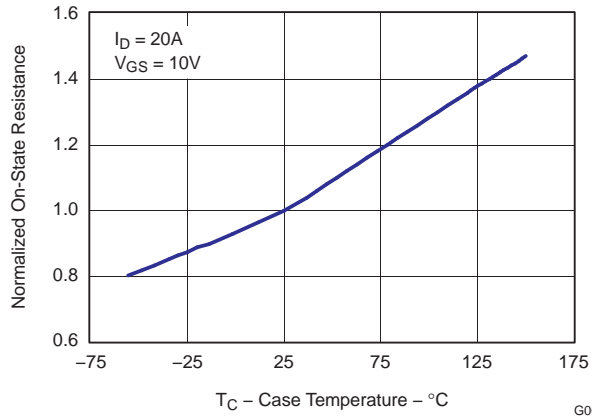


Figure 8. On Resistance vs Temperature

G007

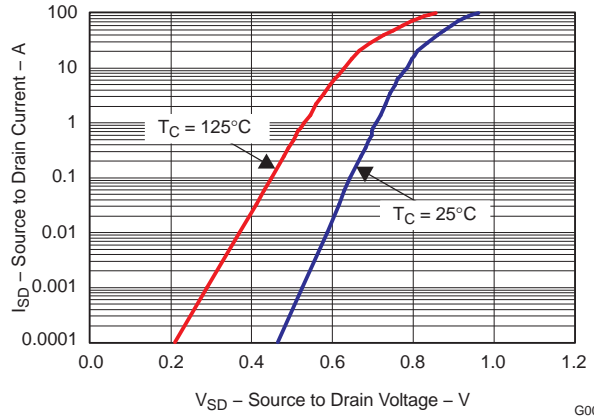


Figure 9. Typical Diode Forward Voltage

G008

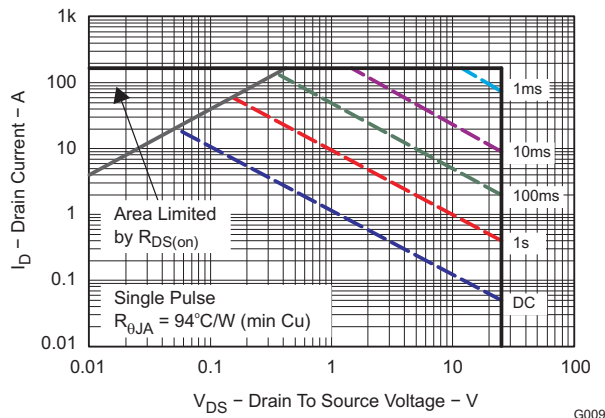


Figure 10. Maximum Safe Operating Area

G009

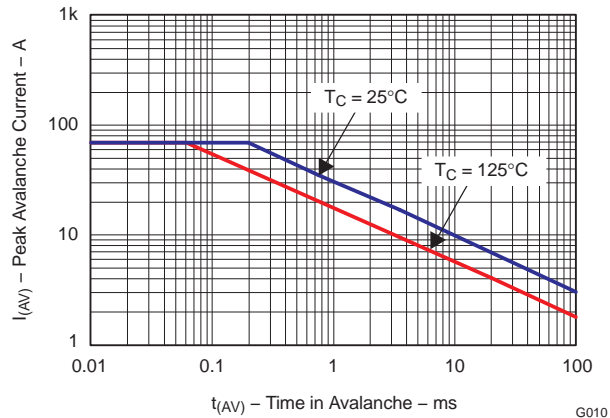


Figure 11. Single Pulse Unclamped Inductive Switching

G010

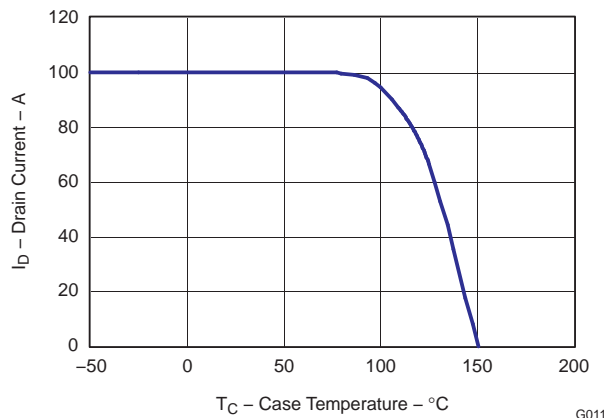


Figure 12. Maximum Drain Current vs Temperature

G011

**MECHANICAL DATA**

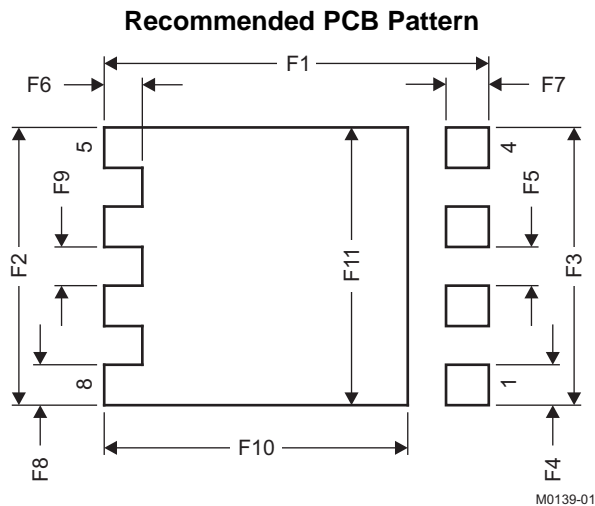
**Q5A Package Dimensions**



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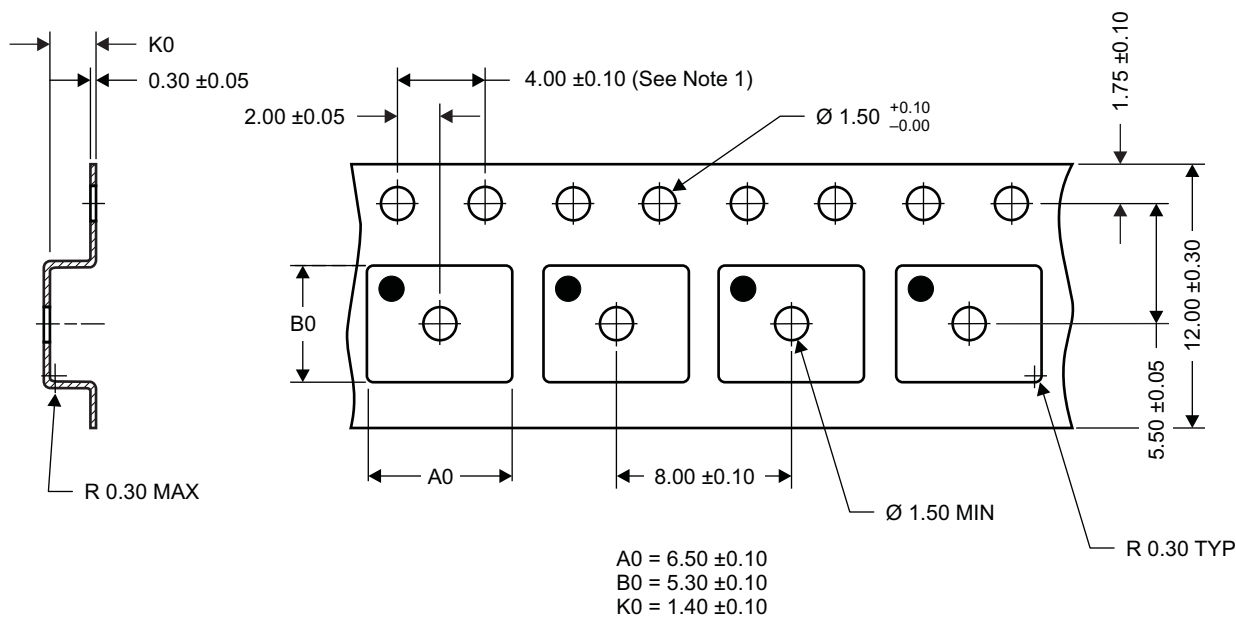
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
c	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
$\theta$	0°		12°

For recommended circuit layout for PCB designs, see application note [SLPA005 – Reducing Ringing Through PCB Layout Techniques](#).



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

**Q5A Tape and Reel Information**



**Notes:**

1. 10 sprocket hole pitch cumulative tolerance ±0.2
2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
3. Material:black static dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified)
5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
6. MSL1 260°C (IR and Convection) PbF Reflow Compatible

**REVISION HISTORY**

**Changes from Original (August 2009) to Revision A**

**Page**

- Deleted the Package Marking Information section ..... 7

## TAPE AND REEL INFORMATION



### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16403Q5A	SON	DQJ	8	2500	330.2	12.4	6.5	5.3	1.4	8.0	12.0	Q1



**TAPE AND REEL BOX DIMENSIONS**



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16403Q5A	SON	DQJ	8	2500	347.0	342.0	55.0

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### Applications

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